



Form 1449 (Modified)	Atty Docket No. NOVLP091	Application No.: 10/820,525
<b>Information Disclosure Statement By Applicant</b>	Applicant: Wu et al.	
(Use Several Sheets if Necessary)	Filing Date 04-07-2004	Group 2812

#### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
<i>SW</i>	A	6,340,628	1/22/02	Van Cleemput, et al.	438	586	12/12/00
<i>SW</i>	B	6,383,955	5/7/02	Matsuki, et al.	438	790	6/7/99
<i>S</i>	C						
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	E						
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#### Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
	J							

#### Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
<i>SW</i>	K	Jan, C.H., et al, <i>90NM Generation, 300mm Wafer Low k ILD/Cu Interconnect Technology</i> , 2003 IEEE Interconnect Technology Conference.
<i>SW</i>	L	U.S. Application No. 10/789,103 (Atty Docket No.: NOVLP094), entitled: METHODS FOR PRODUCING LOW-K CDO FILMS WITH LOW RESIDUAL STRESS, Wu et al.
<i>SW</i>	M	U.S. Application No. 10/800,409 (Atty Docket No.: NOVLP098), entitled: METHODS FOR PRODUCING LOW-K CDO FILMS, Wu et al.
Examiner <i>Andrew J. Hallenbeck</i>		Date Considered <i>09/10/2004</i>

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub- class	Filing Date
<i>[Handwritten signature]</i>	A1	6,329,017	12.11.01	Liu et al.	427	240	10/04/99
	A2	6,383,466	05.07.02	Domansky et al.	423	335	12/28/98
	A3	6,365,266	04.02.02	MacDougall et al.	428	304.4	02/03/00
	A4	5,504,042	04.02.96	Cho et al.	438	781	02/03/94
	A5	5,858,457	01.12.96	Brinker et al.	427	162	09/25/97
	A6	6,270,846	08.07.01	Brinker et al.	428	64.1	09/02/00
	A7	6,387,453	05.14.02	Brinker et al.	427	557	09/02/00
	A8	5,789,027	08.04.98	Watkins et al.	427	250	11/12/96
	A9	6,391,932 B1	05.21.02	Gore et al.	521	01	08/08/00
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	A13	6,596,654	07.22.03	Bayman, et al.	438	788	11/28/01
	A14	4,885,262	12.05.89	Ting et al.			
	A15	5,686,054	11.11.97	Barthel et al.			
	A16	5,851,715	12.22.98	Barthel et al.			
	A17	6,140,252	10.31.00	Cho et al.			
	A18	6,392,017	05.21.02	Chandrashekar			
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Examiner <i>[Handwritten signature]</i>	Date Considered <i>[Handwritten signature]</i>						

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	A38	6,177,329	01.23.01	Pang				
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#### Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
JN	B1	WO95/07543	03.16.95	WIPO			X	
Examiner				Date Considered				
Julian J. Halderson				09/02/04				

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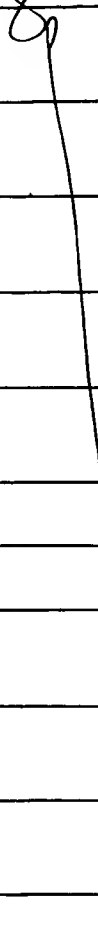

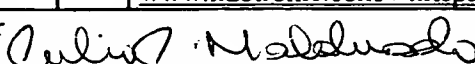
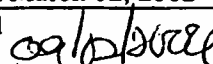
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<i>gk</i>	C1	Cho et al., "Plasma Treatments of Molecularly Templated Nanoporous Silica Films," Electrochemical and Solid-State Letters, 4 (4) G35-G38 (2001)
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	C4	Watkins et al., "Mesoporous Materials and Methods," U.S. Patent Application No. 10/301,013, filed November 21, 2002, 34 Pages
	C5	Justin F. Gaynor, "In-Situ Treatment of Low-K Films With a Silylating Agent After Exposure To Oxidizing Environments," U.S. Patent Application No. 10/056,926 filed January 24, 2002, 34 Pages
	C6	Humayun et al., "Method for Forming Porous Films By Porogen Removal Combined With In SITU Surface Modification", Novellus Corporation, Application No. 10/404,693, filed 3/31/03, pages 1-32. Atty. Docket No. NOVLP064/NVLS-0007
	C7	Tipton et al., "Method Of Porogen Removal From Porous Low-K Films Using UV Radiation", Novellus Systems, Inc., Application No. 10/672,311, filed 9/26/03, pages 1-27. Atty. Docket No. NOVLP075/NVLS-000820
	C8	U.S. Patent Application No. 10/016,017, File Date: December 12, 2001 (Atty Dkt: NOVLP030)
	C9	U.S. Patent Application No. 10/125,614, File Date: April 18, 2002 (Atty Dkt: NOVLP028)
	C10	U.S. Patent Application No. 10/202,987, File Date: July 23, 2002 (Atty Dkt: NOVLP028X1)
	C11	Tipton et al., "Method for Removal of Porogens From Porous Low-K Films Using Supercritical Fluids", Novellus Systems, Inc., Application No. 10/672,305, filed 9/26/03, pages 1-32. Atty. Docket No. NOVLP069/NVLS-000821
	C12	Gangpadhyay et al., "The First International Surface Cleaning Workshop," Northeastern University, November 11-14, 2002
<i>gk</i>	C13	Cho et al., "Method and Apparatus for UV Exposure of Low Dielectric Constant Materials for Porogen Removal and Improved Mechanical Properties", Novellus Systems, Inc., Application No. 10/800,377, filed 3/11/04, pages 1-31. Atty. Docket No. NOVLP089/NVLS-2887
Examiner <i>Julius A. [Signature]</i>	Date Considered <i>09/02/2004</i>	

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	C14	Wu et al., "Method and Apparatus of UV Exposure of Low Dielectric Constant Materials for Porogen Removal and Improved Mechanical Properties", Novellus Systems, Inc., Application No. 10/807,680, filed 3/23/04, pages 1-34. Atty. Docket No. NOVLP097/NVLS-2906
	C15	Humayun et al., "Method For Forming Porous Films By Porogen Removal Combined With In Situ Modification", U.S. Patent No. 10/404,693, filed March 31, 2003, Office Action dated March 15, 2005 (Atty Dkt: NOVLP064)
	C16	Tipton et al., "Method Of Porogen Removal From Porous Low-K Films Using UV Radiation", U.S. Application No. 10/672,311, filed September 26, 2003, Office Action dated September 7, 2004 (Atty Dkt: NOVLP075/NVLS-000820)
	C17	Tipton et al., "Method Of Porogen Removal From Porous Low-K Films Using UV Radiation", U.S. Application No. 10/672,311, filed September 26, 2003, Office Action dated December 28, 2004 (Atty Dkt: NOVLP075/NVLS-000820)
	C18	Tipton et al., "Method For Removal Of Porogens From Porous Low-K Films Using Supercritical Fluids", U.S. Patent No. 10/672,305, Office Action dated March 22, 2005 (Atty Dkt: NOVLP069).
	C19	Bandyopadhyay et al., "Method to Improve Mechanical Strength of Low-K Dielectric Film Using Modulated UV Exposure", U.S. Patent Application No. 10/825,888, filed April 16, 2004 (Atty Dkt: NOVLP088US/NVLS-2882)
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	C21	Jin et al., "Nanoporous Silica as an Ultralow-k Dielectric," MRS Bulletin, October 1997, Pages 39-42
	C22	Asoh et al., "Fabrication of Ideally Ordered Anodic Porous Alumina with 63 nm Hole Periodicity Using Sulfuric Acid," J. Vac. Sci. Technol. B 19(2), Mar/Apr 2001, Pages 569-572
	C23	Asoh et al., "Conditions for Fabrication of Ideally Ordered Anodic Porous Alumina Using Pretextured Al," Journal of the Electrochemical Society, 148 (4) B152-B156 (2001) Pages B152-B156
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	C25	Masuda et al. "Highly Ordered Nanochannel-Array Architecture in Anodic Alumina," App. Phys. Lett. 71(19), November 1997, Pages 2770-2772
	C26	Clube et al., "White Paper from Holotronic Technologies SA; downloaded from <a href="http://www.hdotronic.com/whitepaper/fine-patt.pdf">www.hdotronic.com/whitepaper/fine-patt.pdf</a> on March 12, 2002
Examiner 	Date Considered 	

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	04-07-2004	2812

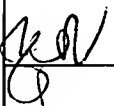
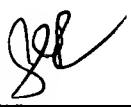


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	C30	"Shipley Claims Porous Low K Dielectric Breakthrough," Press Release March 17, 2003.
	C31	Jeffrey M. Calvert and Michael K. Gallagher, Semiconductor International, 26 (12), 56 (2003).
	C32	Van Bavel et al., Future Fab International, 16, (2004).
	C33	Caluwaerts et al, "Post Patterning Meso Porosity Creation: A Potential Solution For Pore Sealing," IITC 2003.
	C34	Peter Singer, "New Materials and Designs to Improve Transistor Performance", April 1, 2004, Semiconductor International.
	C35	Ghani et al, "A 90nm High Volume Manufacturing Logic Technology Featuring Novel 45nm Gate Length Strained Silicon CMOS Transistors", IEEE, © 2003.
	C36	Bhadri N. Varadarajan, "Tensile Silicon Nitride – P1264 NESL", C & F Study, August 21, 2003.
	C37	Varadarajan, et al., "Strained Transistor Architecture and Method", Novellus Systems, Inc., Appln No. 10/923,259, filed August 20, 2004, pages 1-24. [Atty Docket No. NOVLP108/NVLS-2933].
	C38	Niu et al., "Methods For Improving The Cracking Resistance Of Low-K Dielectric Materials", U.S. Application No. 10/860,340, filed June 2, 2004, (Atty Dkt: NOVLP099)
	C39	Niu et al., "Methods For Improving The Cracking Resistance Of Low-K Dielectric Materials", U.S. Application No. 10/860,340, Office Action dated March 2, 2005, (Atty Dkt: NOVLP099)
	C40	Niu et al., "Methods For Improving The Cracking Resistance Of Low-K Dielectric Materials", U.S. Application No. 10/860,340, Final Office Action dated June 13, 2005, (Atty Dkt: NOVLP099)
	C41	Wang et al., "Plasma Detemplating And Silanol Capping Of Porous Dielectric Films", U.S. Application No. 10/785,235, filed February 23, 2004 (Atty Dkt: NOVLP085)
	C42	Varadarajan et al., "Tensile Dielectric Films Using UV Curing", U.S. Application No. 10/972,084, filed October 22, 2004 (Atty Dkt: NOVLP122)
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Examiner	Date Considered	
Lucien Halderman		09/12/2004

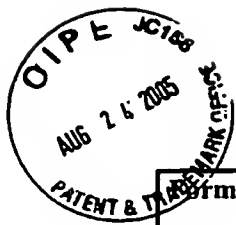
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Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	C44	Fox et al., "Methods For Producing Low-Stress Carbon-Doped Oxide Films With Improved Integration Properties", U.S. Application No. 10/987,208, filed November 12, 2004 (Atty Dkt: NOVLP104)
	C45	Van Den Hoek et al., "VLSI Fabrication Processes For Introducing Pores Into Dielectric Materials," U.S. Application No. 11/050,621, filed January 31, 2005 (Atty Dkt: NOVLP100)
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	C49	Cho et al., "Methods of Improving Porogen Removal and Film Mechanical Strength in Producing Ultra Low-K Carbon Doped Oxide Films Using Radical Photopolymerization", U.S. Application No. 10/982,654, filed November 5, 2004 (Atty Dkt: NOVLP115)
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**U.S. Patent Documents**

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
	A1	6,500,770 B1	12.2002	Cheng et al.	438	762	04/24/02
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							Yes	No

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	C2	U.S. Office Action mailed July 27, 2005, from U.S Application No. 10/785,235 [Atty Dkt No. NOVLP085/NVLS-2875].
Examiner		Date Considered 09/21/06

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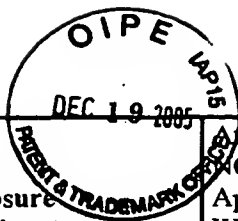
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	C2	U.S. Office Action mailed September 1, 2005, from U.S Application No. 10/672,305 [Atty Dkt No. NOVLP069/NVLS-000821].
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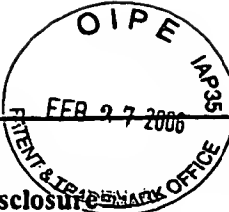
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#### Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
jal	C1	Cho et al., "Method for Porogen Removal and Mechanical Strength Enhancement of Low-K Carbon Doped Silicon Oxide Using Low Thermal Budget Microwave Curing", U.S. Application No. 11/280,113, filed November 15, 2005 (Atty Dkt: NOVLP145/NVLS-3106)
Examiner: <i>Guilherme M. de Almeida</i>		Date Considered: <i>09/16/06</i>

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Foreign Patent or Published Foreign Patent Application								
Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No

Other Documents		
Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
[Signature]	C1	U.S. Office Action mailed December 27, 2005, from U.S. Application No. 10/789,103 [Atty Dkt No. NOVLP094/NVLS-002919].
	C2	U.S. Office Action mailed December 23, 2005, from U.S. Application No. 10/800,409 [Atty Dkt No. NOVLP098/NVLS-002907].
	C3	U.S. Office Action mailed February 7, 2006, from U.S. Application No. 10/672,305 [Atty Dkt No. NOVLP069/NVLS-000821].
	C4	U.S. Office Action mailed December 20, 2005, from U.S. Application No. 10/672,311 [Atty Dkt No. NOVLP075/NVLS-000820].
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[Signature]	C6	U.S. Office Action mailed January 9, 2006, from U.S. Application No. 10/785,235 [Atty Dkt No. NOVLP085/NVLS-2875].
Examiner <u>[Signature]</u>		Date Considered <u>09/10/06</u>

Examiners: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



Form 1449 (Modified)	Atty Docket No. NOVLP091	Application No.: 10/820,525
<b>Information Disclosure Statement By Applicant</b>	Applicant: Wu et al.	
(Use Several Sheets if Necessary)	Filing Date 04-07-2004	Group 2812 3803

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**Foreign Patent or Published Foreign Patent Application**

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No

**Other Documents**

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
<i>[Signature]</i>	C1	Subramonium et al., "Pulsed PECVD Method for Modulating Hydrogen Content in Hard Mask", U.S. Application No. 11/318,269, filed December 23, 2005 (Atty Dkt: NOVLP144/NVLS-3102)
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Examiner <i>[Signature]</i>		Date Considered <i>07/02/06</i>

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



<b>Form 1449 (Modified)</b>  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)	Atty Docket No. NOVLP091 Applicant: Wu et al. Filing Date 04-07-2004	Application No.: 10/820,525  Group 2812 2823
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Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
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	C2	U.S. Office Action mailed May 30, 2006, from U.S. Application No. 10/785,235 [Atty Dkt No. NOVLP085/NVLS-2875].
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Examiner	Julius M. Mahmood	
Date Considered	07/02/2006	

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.